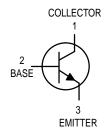
BC237,A,B,C

BC238B,C BC239,C

CASE 29-04, STYLE 17 TO-92 (TO-226AA)

Amplifier Transistors NPN Silicon



MAXIMUM RATINGS

Rating	Symbol	BC 237	BC 238	BC 239	Unit
Collector-Emitter Voltage	VCEO	45 25 25		Vdc	
Collector-Emitter Voltage	VCES	50	30	30	Vdc
Emitter-Base Voltage	VEBO	6.0	5.0	5.0	Vdc
Collector Current — Continuous	IC	100		mAdc	
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8			mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.0 8.0		Watts mW/°C	
Operating and Storage Junction Temperature Range	T _J , T _{Stg}	-55 to +150			°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Thermal Resistance, Junction to Case	$R_{ heta JC}$	125	°C/W

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS							
Collector-Emitter Breakdown Voltage (I _C = 2.0 mA, I _B = 0)	BC237 BC238 BC239	V(BR)CEO	45 25 25	_ _ _	_ _ _	V	
Emitter-Base Breakdown Voltage (I _E = 100 μA, I _C = 0)	BC237 BC238 BC239	V(BR)EBO	6.0 5.0 5.0	_ _ _	_ _ _	V	
Collector Cutoff Current (VCE = 30 V, VBE = 0)	BC238 BC239	CES		0.2 0.2	15 15	nA	
$(V_{CE} = 50 \text{ V}, V_{BE} = 0)$	BC237		_	0.2	15		
(V _{CE} = 30 V, V _{BE} = 0) T _A = 125°C	BC238 BC239		_ _	0.2 0.2	4.0 4.0	μΑ	
$(V_{CE} = 50 \text{ V}, V_{BE} = 0) \text{ T}_{A} = 125^{\circ}\text{C}$	BC237		_	0.2	4.0		

BC237,A,B,C BC238B,C BC239,C

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted) (Continued)

Characteristic		Symbol	Min	Тур	Max	Unit
ON CHARACTERISTICS					•	
DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V)	BC237A BC237B/238B BC237C/238C/239C	hFE	_ _ _	90 150 270	_ _ _	_
$(I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC237 BC239 BC237A BC237B/238B BC237C/238C/239C		120 120 120 200 380	— 170 290 500	800 800 220 460 800	
$(I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V})$	BC237A BC237B/238B BC237C/238C/239C		_ _ _	120 180 300	_ _ _	
Collector-Emitter On Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)	BC237/BC238/BC239 BC237/BC239 BC238	VCE(sat)	_ _	0.07 0.2	0.2 0.6 0.8	V
Base-Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA)		V _{BE(sat)}	_ _	0.6 —	0.83 1.05	V
Base–Emitter On Voltage ($I_C = 100 \mu A$, $V_{CE} = 5.0 V$) ($I_C = 2.0 mA$, $V_{CE} = 5.0 V$) ($I_C = 100 mA$, $V_{CE} = 5.0 V$)		VBE(on)	 0.55 	0.5 0.62 0.83	 0.7 	V
DYNAMIC CHARACTERISTICS					•	
Current-Gain — Bandwidth Product (I _C = 0.5 mA, V _{CE} = 3.0 V, f = 100 MHz)	BC237 BC238 BC239	fΤ	_ _ _	100 120 140	_ _ _	MHz
$(I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 100 \text{ MHz})$	BC237 BC238 BC239		150 150 150	200 240 280	_ _ _	
Collector–Base Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)		C _{obo}	_	_	4.5	pF
Emitter–Base Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)		C _{ibo}	_	8.0	_	pF
Noise Figure (IC = 0.2 mA, VCE = 5.0 V, RS = 2.0 k Ω , f = 1.0 kHz)	BC239	NF	_	2.0	4.0	dB
(I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2.0 kΩ, f = 1.0 kHz, Δ f = 200 Hz)	BC237 BC238 BC239		_ _ _	2.0 2.0 2.0	10 10 4.0	

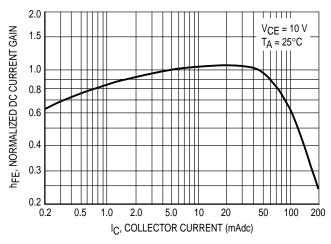


Figure 1. Normalized DC Current Gain

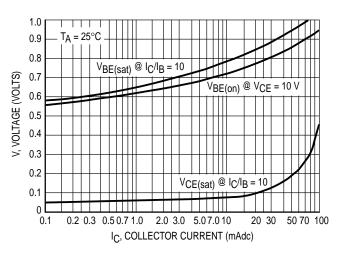


Figure 2. "Saturation" and "On" Voltages

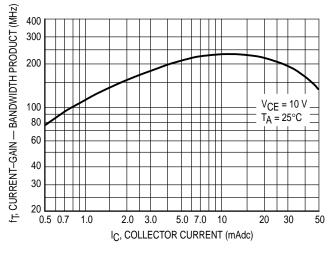


Figure 3. Current-Gain — Bandwidth Product

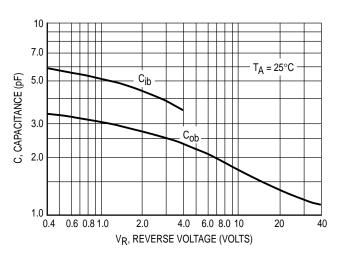


Figure 4. Capacitances

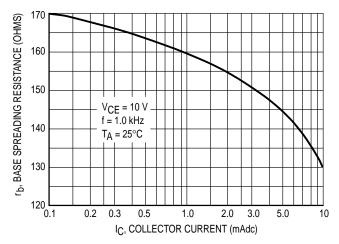
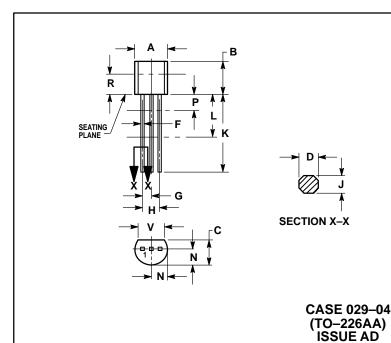


Figure 5. Base Spreading Resistance

PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN P AND L. DIMENSION F APPLIES BETWEEN F AIND L.
 DIMENSION D AND J APPLY BETWEEN L AND K
 MINIMUM. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.175	0.205	4.45	5.20	
В	0.170	0.210	4.32	5.33	
С	0.125	0.165	3.18	4.19	
D	0.016	0.022	0.41	0.55	
F	0.016	0.019	0.41	0.48	
G	0.045	0.055	1.15	1.39	
Н	0.095	0.105	2.42	2.66	
J	0.015	0.020	0.39	0.50	
K	0.500		12.70		
L	0.250		6.35		
N	0.080	0.105	2.04	2.66	
Р		0.100	_	2.54	
R	0.115		2.93		
V	0.135		3 43		

STYLE 17:

PIN 1. COLLECTOR 2. BASE

- 3. **EMITTER**

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